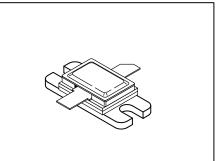
The RF Line Microwave Pulse Power Transistor

Designed for 1025–1150 MHz pulse common base amplifier applications such as TACAN and DME.

- Guaranteed Performance @ 1090 MHz
 Output Power = 375 Watts Peak
 Gain = 6.7 dB Min 7.5 dB (Typ)
- 100% Tested for Load Mismatch at All Phase Angles with 3:1 VSWR
- Hermetically Sealed Package
- Silicon Nitride Passivated
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration
- Internal Input Matching
- Characterized using 10 μs, 1% Duty Pulse Format



375 W (PEAK), 1025–1150 MHz MICROWAVE POWER TRANSISTOR NPN SILICON



CASE 355G-01, STYLE 1

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCES	70	Vdc
Collector–Base Voltage	V _{CBO}	70	Vdc
Emitter-Base Voltage	VEBO	4.0	Vdc
Collector Current — Peak (1)	ι _C	29	Adc
Total Device Dissipation @ $T_C = 25^{\circ}C$ (1) (2) Derate above $25^{\circ}C$	PD	1458 8.33	Watts W/°C
Storage Temperature Range	T _{stg}	- 65 to +200	°C
Junction Temperature	Тј	200	°C

Rating	Symbol	Мах	Unit
Thermal Resistance, Junction to Case (3) (4)	R _θ JC	0.12	°C/W

NOTES:

1. Under pulse RF operating conditions.

2. These devices are designed for RF operation. The total device dissipation rating applies only when the devices are operated as pulsed RF amplifiers.

3. Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques.

4. Pulse Width = 10 $\mu s,$ Duty Cycle = 1%.



ELECTRICAL CHARACTERISTICS (T_C = 25° C unless otherwise noted.)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•		•
Collector–Emitter Breakdown Voltage ($I_C = 60 \text{ mAdc}, V_{BE} = 0$)	V(BR)CES	70	-	—	Vdc
Collector–Base Breakdown Voltage ($I_C = 60 \text{ mAdc}, I_E = 0$)	V _(BR) CBO	70	-	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \text{ mAdc}, I_C = 0$)	V(BR)EBO	4.0	—	-	Vdc
Collector Cutoff Current ($V_{CB} = 50$ Vdc, $I_E = 0$)	ICBO	_	—	3.0	mAdc
ON CHARACTERISTICS	-				
DC Current Gain (I _C = 5.0 Adc, V_{CE} = 5.0 Vdc)	h _{FE}	10	-	-	-
FUNCTIONAL TESTS	-				
Common–Base Amplifier Power Gain (V _{CC} = 50 Vdc, P _{out} = 375 W Peak, f = 1090 MHz)	G _{PB}	6.7	7.5	-	dB
Collector Efficiency (V _{CC} = 50 Vdc, P _{out} = 375 W Peak, f = 1090 MHz)	ης	40	-	-	%
Load Mismatch (V _{CC} = 50 Vdc, P _{out} = 375 W Peak, f = 1090 MHz, Load VSWR = 3:1 All Phase Angles)	Ψ	N	Degradation	in Output Po	wer

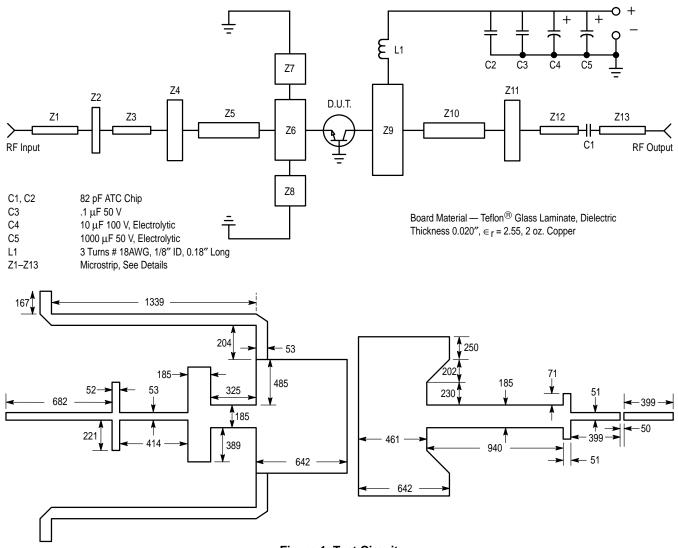


Figure 1. Test Circuit

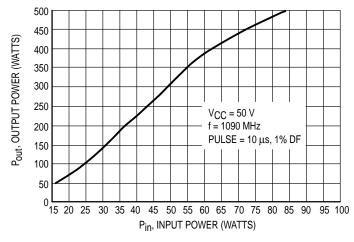


Figure 2. Output Power versus Input Power

-		
Freq MHz	Z _{in} Ohms	Z _{OL} * Ohms (1)
1025	2.4 + j1.7	1.1 + j1.3
1050	2.1 + j1.2	1.1 + j1.4
1090	1.8 + j1.1	1.1 + j1.3
1125	1.6 + j1.1	1.3 + j1.3
1150	1.4 + j1.0	1.2 + j1.6

(1) Z_{OL}* is the conjugate of the optimum load impedance into which the device operates at a given output power voltage and frequency.

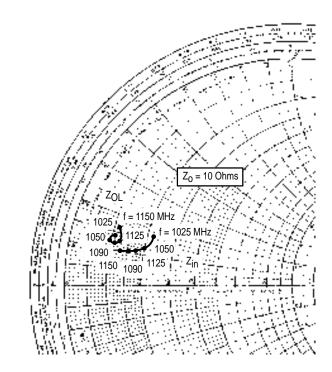
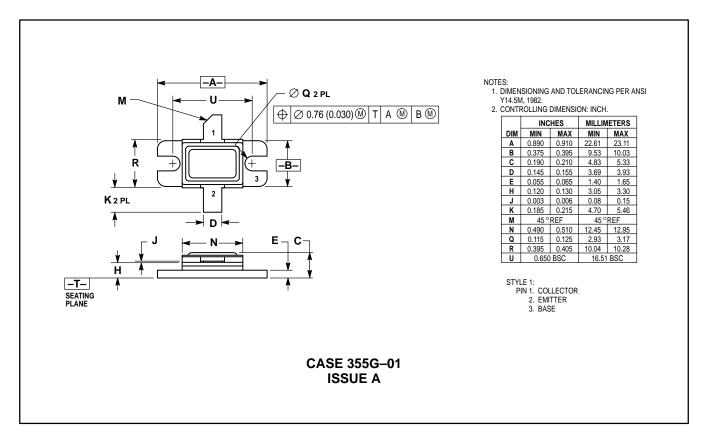


Figure 3. Series Equivalent Input/Output Impedances

PACKAGE DIMENSIONS



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